

### General Features

- $V_{DS} = 20V, I_D = 6A$
- $R_{DS(ON)} < 23m\Omega @ V_{GS}=2.5V$
- $R_{DS(ON)} < 35m\Omega @ V_{GS}=4.5V$

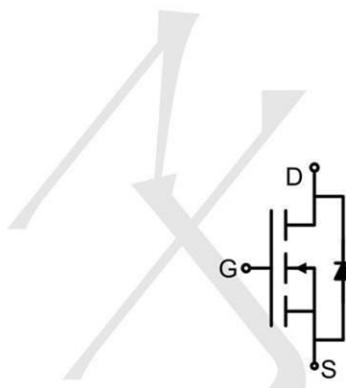
### Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable
- Logic Level Shift

### Package and Pin Configuration



Circuit diagram



### Marking:



“P” is TECHPUBLIC LOGO  
“XXXX” Marking ID (Please see the last page for details )

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	
Continuous Drain Current	$I_D$	6	A
Continuous Source-Drain Current(Diode Conduction)	$I_S$	0.6	
Power Dissipation	$P_D$	1.25	W
Thermal Resistance from Junction to Ambient ( $t \leq 5s$ )	$R_{\theta JA}$	312.5	$^\circ C/W$
Operating Junction	$T_J$	150	$^\circ C$
Storage Temperature	$T_{STG}$	-55 ~ +150	



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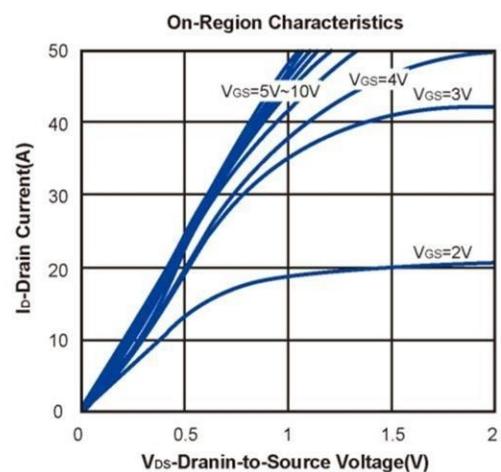
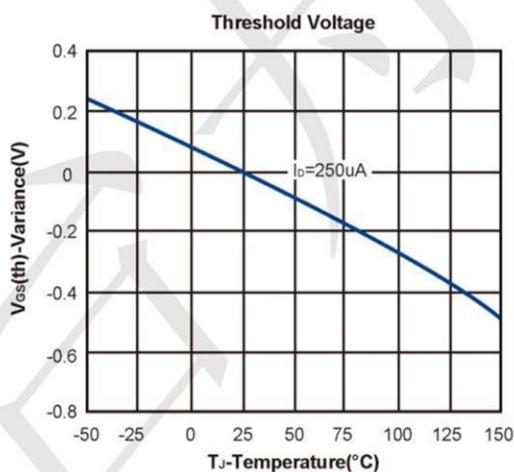
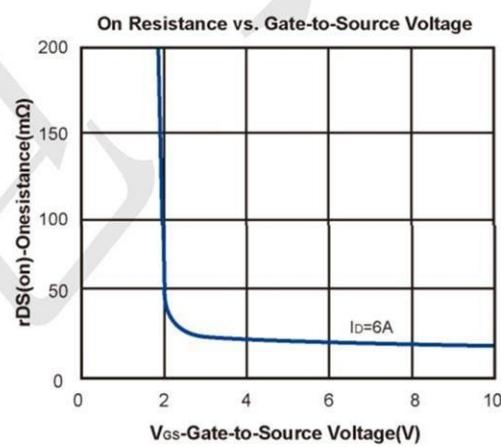
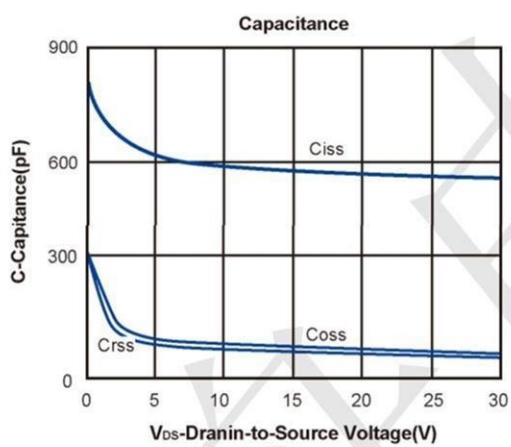
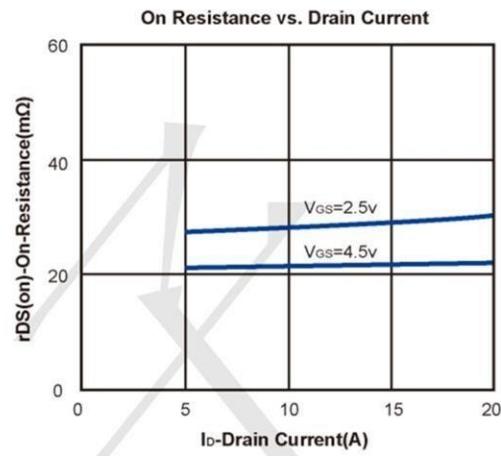
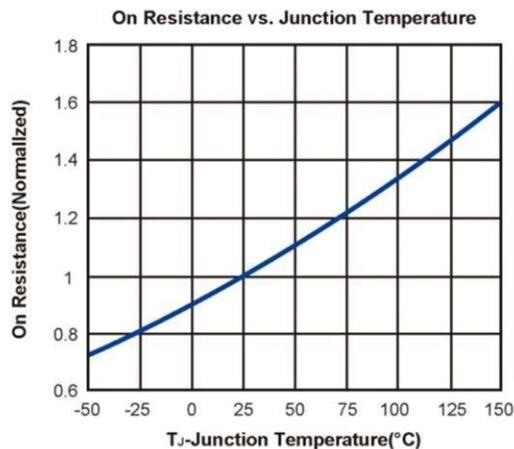
**N-Channel MOSFET**

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**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static</b>						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 10\mu\text{A}$	20			V
Gate-threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 50\mu\text{A}$	0.40		1	
Gate-body leakage	$I_{\text{GSS}}$	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 8\text{V}$			$\pm 100$	nA
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$			1	$\mu\text{A}$
Drain-source on-resistance <sup>a</sup>	$r_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 6\text{A}$		0.021	0.023	$\Omega$
		$V_{\text{GS}} = 2.5\text{V}, I_{\text{D}} = 5.2\text{A}$		0.028	0.035	
Forward transconductance <sup>a</sup>	$g_{\text{fs}}$	$V_{\text{DS}} = 5\text{V}, I_{\text{D}} = 3.6\text{A}$		8		S
Diode forward voltage	$V_{\text{SD}}$	$I_{\text{S}} = 0.94\text{A}, V_{\text{GS}} = 0\text{V}$		0.74	1.2	V
<b>Dynamic</b>						
Total gate charge	$Q_g$	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 3.6\text{A}$		7.7	10	nC
Gate-source charge	$Q_{\text{gs}}$			0.32		
Gate-drain charge	$Q_{\text{gd}}$			2.1		
Input capacitance <sup>b</sup>	$C_{\text{iss}}$	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		574		pF
Output capacitance <sup>b</sup>	$C_{\text{oss}}$			70		
Reverse transfer capacitance <sup>b</sup>	$C_{\text{rss}}$			60		
<b>Switching<sup>b</sup></b>						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 10\text{V}, R_L = 5.5\Omega, I_{\text{D}} \approx 3.6\text{A}, V_{\text{GEN}} = 4.5\text{V}, R_g = 6\Omega$		78.7		ns
Rise time	$t_r$			128		
Turn-off delay time	$t_{\text{d}(\text{off})}$			453		
Fall time	$t_f$			80.9		

### Typical Electrical and Thermal Characteristics





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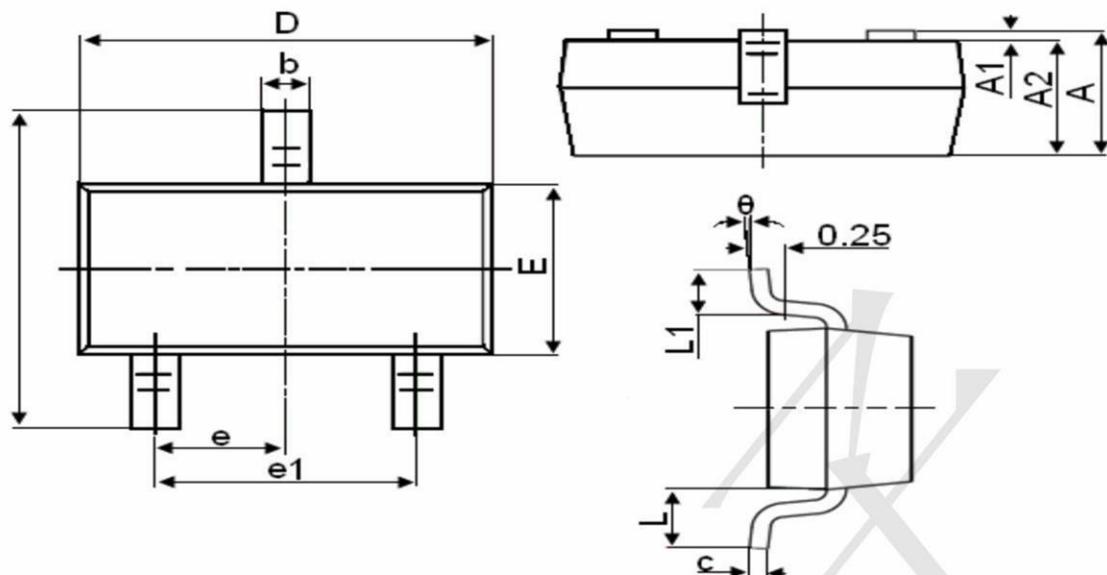
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**DMN2041L**

**100V 3.5A N-Channel MOSFET**

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### Package Outline Dimensions (SOT-23)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

### Marking:



**"P"** is TECHPUBLIC LOGO  
**"V6"** is Part number,fixed  
**"xx"** is internal code